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- **High Voltage Power Devices (HV):** High voltage silicon based discrete devices (>200V) such as super junction MOSFETs, IGBTs, thyristors, GTOs and pn-diodes.
- **Low Voltage Power Devices and Power IC Technology (LVT):** Low voltage silicon based discrete power devices (≤200V) and power devices for power ICs of all voltage ranges.
- **Power IC Design (ICD):** Circuit design and demonstration using power IC technology platform.
- **GaN and II/III/V Compound Materials (GaN):** GaN and other III/V compound material (e.g. AlN, GaAs) based power devices, technology and integration, materials, and processing.
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- **Module and Package Technologies (PK):** Module and package technology for discrete power devices and power ICs.

**ABSTRACT SUBMISSION:**

- **Abstract Submission Deadline:** November 8, 2019
- **Author Notification:** January 20, 2020
- **Late News Submission (limited acceptance):** February 28, 2020
- **Final Manuscript Submission Deadline:** March 13, 2020
- **Submission Requirements:** A PDF abstract should be submitted through the website including a single page text summary in English (500 words maximum) and up to two additional pages of supporting figures.

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